SPECIFICATION AMENDMENTS:

Please amend the specification as follows:

Please replace paragraph [0005] with the following replacement paragraph:

The P-Type lightly doped (P-) polysilicon layer 140 is deposited on the dielectric layer 130 and ~~is~~ further ~~defined~~ defines a plurality of parallel, separate bit lines (BL)~~, such as bit lines 142a, 142b in FIG. 1~~. The bit lines ~~142a, 142b~~ overlap the word lines 122a, 122b, 122c, from a top view, to form a shape approximating ~~approximately as~~ a cross.

Please replace paragraph [0018] with the following replacement paragraph:

-- FIG. 2A is a cross-sectional view showing a 3D polysilicon ROM of the first example of the invention. Referring ~~first~~ to FIG. 2A and FIG. 2H, a 3D polysilicon read only memory (ROM) 20 includes a silicon substrate 210, an isolated silicon dioxide (SiO_2) layer 211, a N-Type heavily doped (N+) polysilicon layer 220, a dielectric layer 230, a P-Type lightly doped (P-) polysilicon layers 240, a first oxide layer 224, and a second oxide layer 244 (shown in FIG. 2H).

Please replace paragraph [0020] with the following replacement paragraph:

The P-Type lightly doped (P-) polysilicon layer 240 is deposited on the dielectric layer 230 and ~~is~~ further ~~defined~~ defines a plurality of parallel, separate bit lines (BL), such as bit lines 242a, 242b in ~~FIG. 2A~~ FIG. 2F. The bit lines 242a, 242b overlap the word lines 222a, 222b, 222c, from a top view, to form a shape ~~approximately as~~ approximating a cross.

Please replace paragraph [0021] with the following replacement paragraph:

-- Moreover, there is at least one neck structure, such as neck 231a, 231b (shown in FIGs. 2G and 2H), individually formed between the N-Type heavily doped (N+) polysilicon layer 220 and the P-Type lightly doped (P-) polysilicon layer 240 by ~~isotropy~~ isotropically etching the dielectric layer. The neck 231a, 231b (shown in FIGs. 2G and 2H) are under the bit lines 242a, 242b, respectively. The second oxide layer 244 is filled in the space between the bit lines 242a, 242b and is on the word lines 222a, 222b, 222c and on the first oxide layer 224. --